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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/646,206	08/22/2003	Steffen Hornig	P2001,0122	P2001,0122 9023		
24131	7590 11/02/2004		EXAM	EXAMINER		
LERNER AND GREENBERG, PA			DOLAN, JE	DOLAN, JENNIFER M		
P O BOX 248	0					
HOLLYWOOD, FL 33022-2480			ART UNIT	PAPER NUMBER		

2813

DATE MAILED: 11/02/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Applicati	on No.	Applicant(s)			
Office Action Summary		10/646,2	06	HORNIG ET AL.			
		Examine	r	Art Unit	· · · · · · · · · · · · · · · · · · ·		
		Jennifer I		2813			
Period fo	The MAILING DATE of this communication a or Reply	ppears on th	e cover sheet with the c	orrespondence addres	ss		
A SH THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REP MAILING DATE OF THIS COMMUNICATION nsions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. Period for reply specified above is less than thirty (30) days, a report of period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by stature to reply within the set or extended period for reply will, by stature the process of the process of the process of the mail and patent term adjustment. See 37 CFR 1.704(b).	1.136(a). In no exemply within the stand will apply and vute, cause the app	rent, however, may a reply be tin tutory minimum of thirty (30) day rill expire SIX (6) MONTHS from blication to become ABANDONE	nely filed s will be considered timely. the mailing date of this commu D (35 U.S.C. § 133).	unication.		
Status							
2a)□	Responsive to communication(s) filed on <u>24 September 2004</u> . This action is FINAL . 2b) This action is non-final. Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dispositi	on of Claims						
5)□ 6)⊠ 7)□	Claim(s) 1-21 is/are pending in the application 4a) Of the above claim(s) is/are withdred Claim(s) is/are allowed. Claim(s) 1-21 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and	awn from co					
Applicati	on Papers						
10)⊠	The specification is objected to by the Examir The drawing(s) filed on <u>22 August 2003</u> is/are Applicant may not request that any objection to th Replacement drawing sheet(s) including the corre The oath or declaration is objected to by the I	e: a) acce ne drawing(s) ection is requi	be held in abeyance. See red if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1			
Priority u	ınder 35 U.S.C. § 119						
12)⊠ a)l	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority documents. 2. Certified copies of the priority documents. 3. Copies of the certified copies of the principle application from the International Bure see the attached detailed Office action for a list	nts have beents have beents have beents	en received. en received in Applicati ents have been receive le 17.2(a)).	on No ed in this National Sta	ge		
2) Notice	t(s) e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 r No(s)/Mail Date 8/22/03.	8) . <i>·</i>	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ite	2)		

DETAILED ACTION

Claim Rejections - 35 USC § 112

- 1. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claim 3 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

The applicant claims "selecting the size of the nanocrystalline particles" with less than a quarter of a wavelength of 248, ..., UV exposure light." It is unclear as to exactly how the size of the particle is selected. For the purposes of examination, it is assumed that the diameter is selected to be less than a quarter of the wavelength of the exposure light.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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4. Claims 1-5, 7-10, 12, 13, 16, 17, 20, and 21 are rejected under 35 U.S.C. 102(b) as being anticipated by European Patent Publication EP 0 744 662 to Kusumoto et al. (cited by applicant).

Regarding claims 1-3 and 20, Kusumoto discloses providing a semiconductor product (page 2, lines 5-14) and coating the product with an anti-reflective coating material formed of a matrix substance (page 3, lines 3-42; page 4, lines 22-30; polymeric materials) and of nanocrystalline particles of a material different from the matrix substance (page 3, lines 17-30), the particles having a diameter of less than 100 nanometers, and thus absorbing light via the quantum size effect (page 3, lines 11-30).

Regarding claims 4, 12, and 13, Kusumoto discloses that the particle material can be titanium oxide (page 3, lines 17-20), which will intrinsically generate the additional energy levels within the band gaps of the matrix substance.

Regarding claim 5, Kusumoto discloses choosing the material of the particles to effect absorption via the quantum size effect of a wavelength in the UV range (page 3, lines 10-30; page 5, lines 45-50).

Regarding claim 7, Kusumoto discloses choosing a material and concentration of particles for tuning a degree of absorption (page 3, lines 10-30; page 4, lines 7-11; column 6, line 50- column 7, line 4; Table 1 (page 10) shows that different compositions lead to different 'reflection preventing' properties).

Regarding claims 8 and 9, Kusumoto discloses choosing the matrix substance and particle size and concentration to tune the viscosity (see page 4, lines 7-11; page 7, lines 45-52; table 1) and the etch resistance of a dry etch process (page 7, lines 35-42; table 1).

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Regarding claim 10, Kusumoto discloses that the matrix substance is an organic resin (page 3, line 30 – page 4, line 45; 'recipes' A-E on pages 8-9).

Regarding claim 16, Kusumoto discloses coating a layer to be patterned on a substrate with the anti-reflective coating to diminish the light reflection of exposure light (page 6, lines 35-60).

Regarding claim 17, Kusumoto discloses, prior to the coating step: providing the matrix material and the particles, and mixing them to form the coating material (pages 3-5, 8-9).

Regarding claim 21, Kusumoto discloses a resist layer on top of the anti-reflective layer (page 6, lines 35-45).

5. Claims 1-6, 10, and 16-20 are rejected under 35 U.S.C. 102(b) as being anticipated by U.S. Patent No. 5,744,293 to Okumura et al. (cited by applicant).

Regarding claims 1-3 and 20, Okumura discloses providing a semiconductor product (column 3, lines 1-25); and coating the semiconductor product with an anti-reflective coating material (14) formed of a matrix substance (column 3, lines 30-48) and of nanocrystalline particles of a material different from the matrix substance (column 3, lines 48-57), the nanocrystalline particles having a diameter of less than 100 nm, and absorbing light via the quantum size effect (column 3, lines 47-65).

Regarding claims 4 and 5, Okumura discloses that the particles are carbon, which automatically creates additional energy levels within band gaps of the matrix (since the material is a semiconductor), thus allowing for absorption of a wavelength in the UV range (column 2, lines 37-60; column 3, lines 52-56).

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Regarding claims 6, 18, and 19, Okumura discloses choosing the matrix substance, particle type, and particle concentration in order to adjust the refractive index relative to the refractive index of the resist layer (column 1, lines 40-46) and the semiconductor substrate, in order to allow for maximum light entrance (i.e. minimum reflection from) into the ARC material (column 2, lines 1-35; column 4, lines 1-9).

Regarding claim 10, Okumura discloses that the matrix is an organic resin (column 3, lines 30-48).

Regarding claim 16, Okumura discloses coating the substrate with the ARC material to diminish reflection of exposure light (see column 1, lines 40-60; column 2, lines 26-60).

Regarding claim 17, Okumura discloses prior to the coating step: providing the matrix material and nano-crystalline particles and mixing the materials to form the antireflective coating (column 3, lines 30-65; column 4, lines 1-20).

Regarding claim 21, Okumura discloses a resist layer on top of the ARC (column 4, lines 28-37).

6. Claims 1, 10, and 11 are rejected under 35 U.S.C. 102(e) as being anticipated by U.S. Patent No. 6,384,318 to Nomura.

Regarding claim 1, Nomura discloses providing a semiconductor product (column 1, lines 35-45); and coating the product with an anti-reflective coating formed of a matrix substance (organic or inorganic binder; see column 2, line 47-column 3, line 12) and nanocrystalline particles of a material different from the matrix substance (see column 2, line 47 – column 3, line 12), the particles being configured to absorb light via the quantum size effect (see column 13,

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lines 29-30; particles with a diameter of 0.05 microns – 0.3 microns would exhibit a quantum size effect).

Regarding claims 10 and 11, Nomura discloses that the matrix substance can be silicon oxide (column 3, lines 5-6).

Claim Rejections - 35 USC § 103

- 7. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 8. Claim 14 is rejected under 35 U.S.C. 102(b) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Kusumoto et al.

Kusumoto discloses that the particle concentration is about 3-20% by weight, which presumably falls within the 3-70% volume concentration specified in the claim.

Assuming arguendo, the 3-20% weight concentration does not intersect the 3-70% volume concentration range.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to specify that the particle concentration in Kusumoto falls into the 3-70% range. The rationale is as follows: A person having ordinary skill in the art would have been motivated to specify a volume concentration of 3-70%, because it would be necessary to provide sufficiently many particles to allow for the absorption of the light, yet few enough to retain the spin coating, etching, and index of refraction properties of the polymeric resin, as is appreciated by one skilled

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in the art. Although Kusumoto does not specify a volume concentration of 3-70%, it has been held that "where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (1955).

9. Claim 15 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kusumoto et al. in view of European Patent Publication EP 0 770 579 to Yamada et al. (cited by applicant).

Kusumoto teaches an antireflective film using titanium oxide particles (see page 3, lines 17-21), but fails to teach a film using two different nanocrystalline particles.

Yamada teaches an antireflective film using nanocrystals of both titanium oxide and another metal oxide (page 5, lines 40-55).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the ARC of Kusumoto by using a second metal oxide nanocrystalline particle, as suggested by Yamada. The rationale is as follows: A person having ordinary skill in the art would have been motivated to use two different nanocrystalline particles, such as titanium oxide and another metal oxide, in the ARC, because doing so increases the photo-responsivity of the ARC as well as enhancing the form of the polymeric coating (see Yamada, page 5, line 19 – page 6, line 26).

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Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jennifer M. Dolan whose telephone number is (571) 272-1690. The examiner can normally be reached on Monday-Friday 8:30am-5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Jennifer M. Dolan Examiner Art Unit 2813

jmd

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